

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

### Product Summary

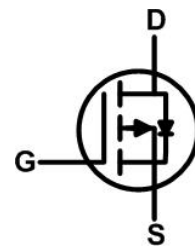
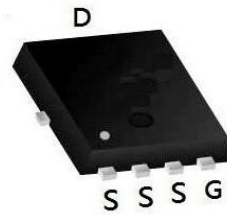


BVDSS	RDSON	ID
-30V	12mΩ	-40A

### Description

The XXW40P03D is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications. The XXW40P03D meet the RoHS and Gree Product requirement 100% EAS guaranteed with full function reliability approved.

### PDFN3333-8L Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		10s	Steady State	
$V_{DS}$	Drain-Source Voltage	-30		V
$V_{GS}$	Gate-Source Voltage	±20		V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-40		A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-25		A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	-120		A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	105		mJ
$I_{AS}$	Avalanche Current	-50		A
$P_D@T_A=25^{\circ}C$	Total Power Dissipation <sup>4</sup>	15		W
$T_{STG}$	Storage Temperature Range	-55 to 150		°C
$T_J$	Operating Junction Temperature Range	-55 to 150		°C

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	66	°C/W

**Electrical Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

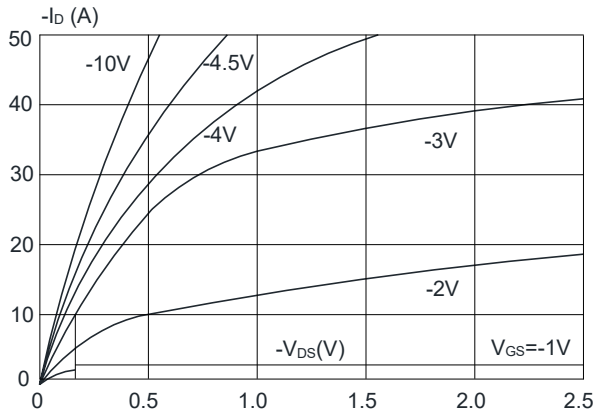
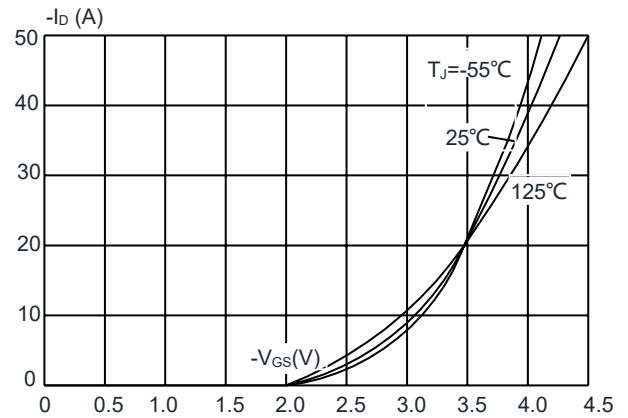
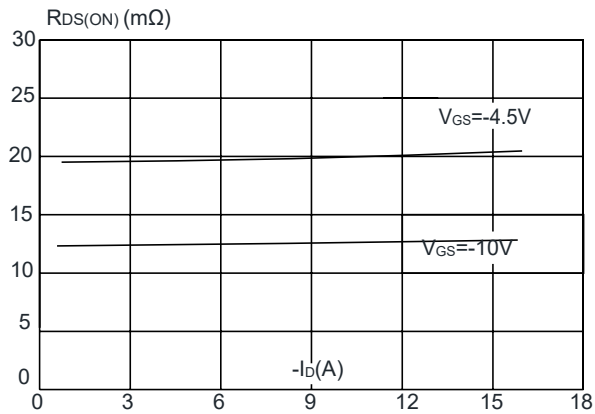
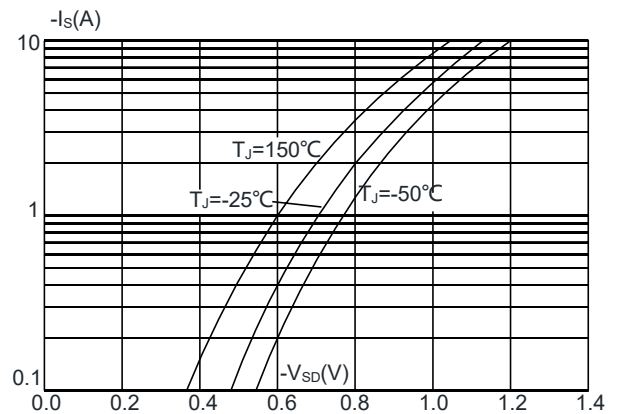
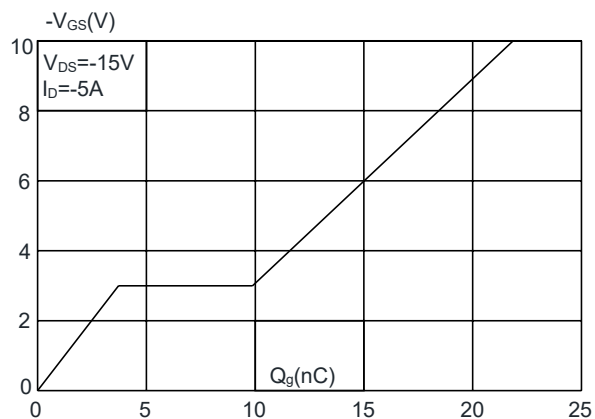
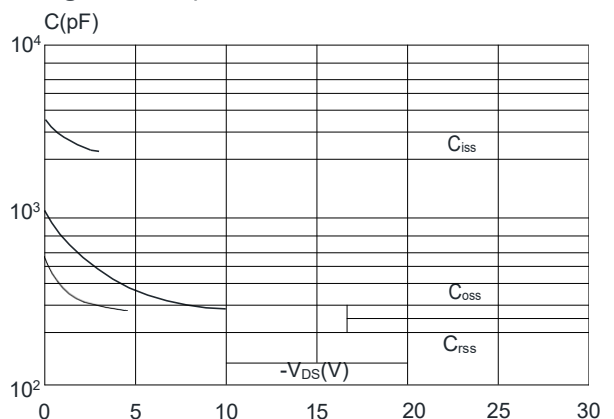
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-30V, V_{GS}=0V,$	-	-	-1	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0	-1.6	-2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance Note3	$V_{GS}=-10V, I_D=-10A$	-	12	15	m $\Omega$
		$V_{GS}=-4.5V, I_D=-5A$	-	18	27	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V,$ $f=1.0MHz$	-	1330	-	pF
$C_{oss}$	Output Capacitance		-	183	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	156	-	pF
$Q_g$	Total Gate Charge	$V_{DS}=-15V, I_D=-5A,$ $V_{GS}=-10V$	-	22	-	nC
$Q_{gs}$	Gate-Source Charge		-	1.0	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	1.8	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=-15V, I_D=-10A,$ $V_{GS}=-10V, R_{GEN}=2.5\Omega$	-	9	-	ns
$t_r$	Turn-on Rise Time		-	13	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	48	-	ns
$t_f$	Turn-off Fall Time		-	20	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	-40	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-90	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=-15A$	-	-0.8	-1.2	V
$t_{rr}$	Reverse Recovery Time	$T_J=25^\circ\text{C},$	-	64	-	ns
$Q_{rr}$	Reverse Recovery Charge	$V_{DD}=-24V, I_F=-2.8A,$ $di/dt=-100A/\mu s$	-	25	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

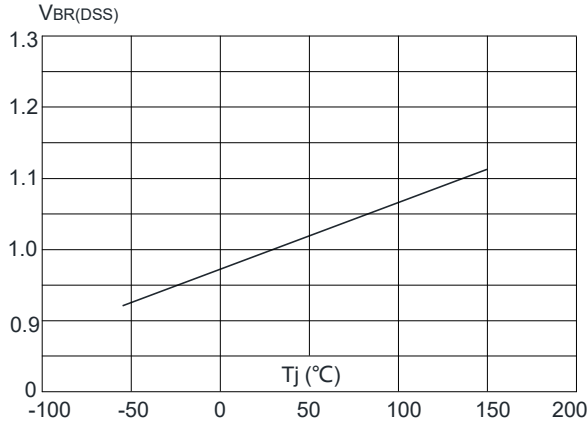
2. EAS condition:  $T_J=25^\circ\text{C}, V_{GS}=10V, R_G=25\Omega, L=0.5mH, I_{AS}=-12.7A$

3. Pulse Test: Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 0.5\%$

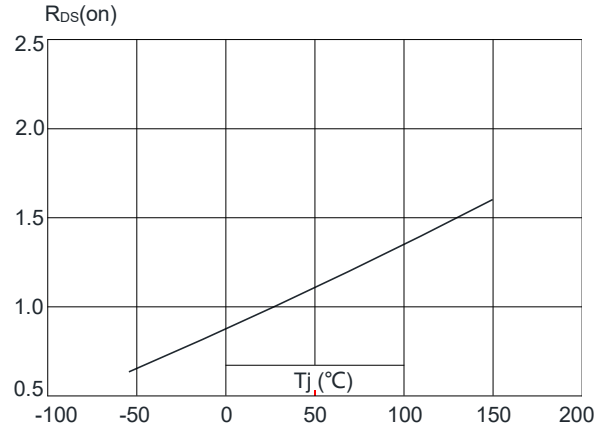
## Typical Performance Characteristics

**Figure 1: Output Characteristics**

**Figure 2: Typical Transfer Characteristics**

**Figure 3: On-resistance vs. Drain Current**

**Figure 4: Body Diode Characteristics**

**Figure 5: Gate Charge Characteristics**

**Figure 6: Capacitance Characteristics**


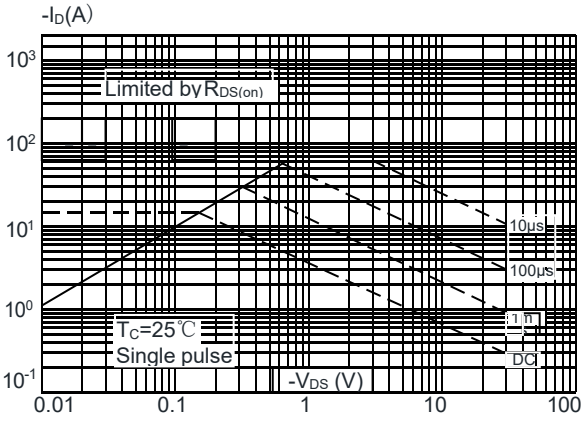
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



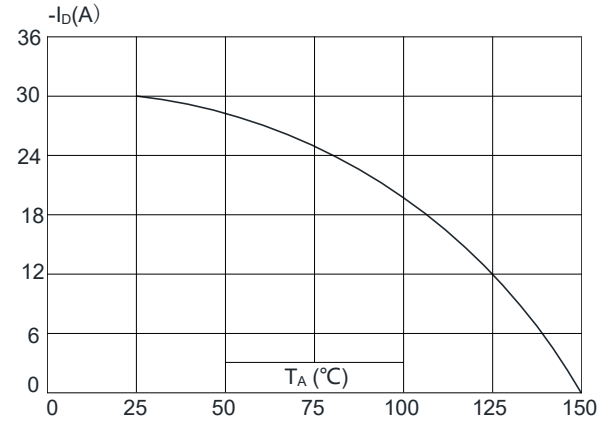
**Figure 8:** Normalized on Resistance vs. Junction Temperature



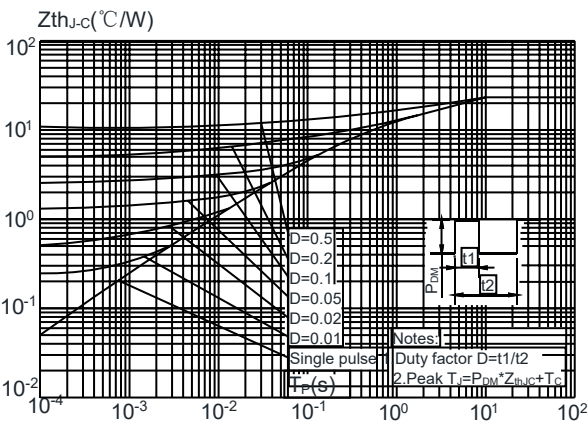
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature

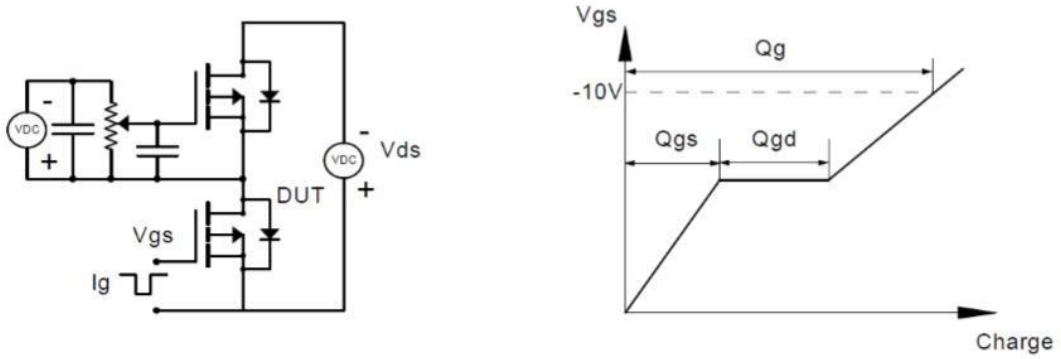


**Figure 11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case

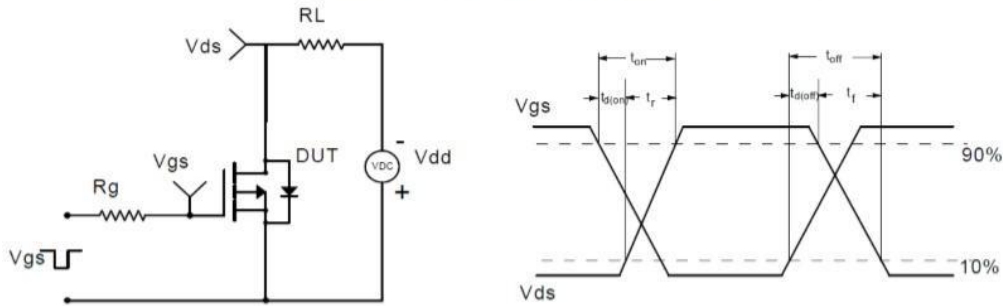


**Test Circuit**

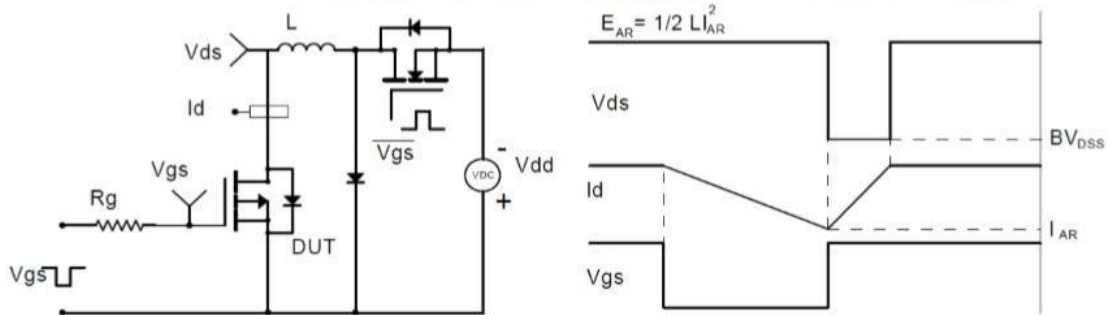
Gate Charge Test Circuit & Waveform



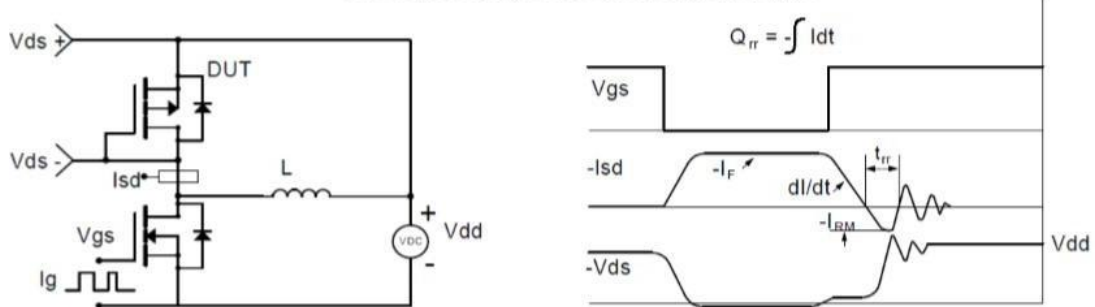
Resistive Switching Test Circuit & Waveforms

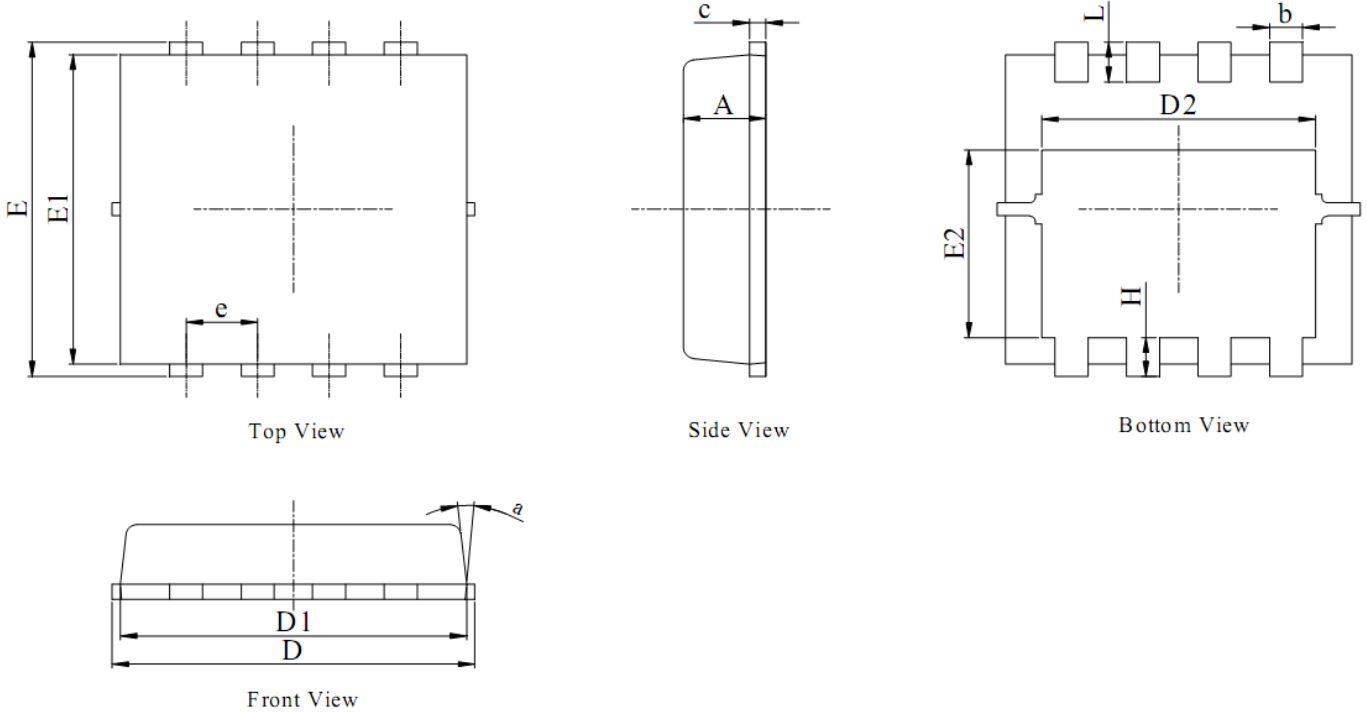


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



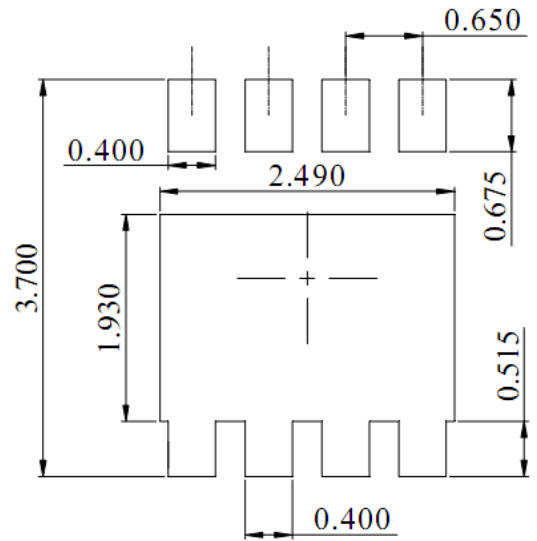
Diode Recovery Test Circuit & Waveforms



**Package Mechanical Data-PDFN3333-8L-Single**

**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. ALL DIMENSIONS IN MILLIMETER (ANGLE IN DEGREE).
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.20	0.25
D	3.00	3.15	3.25
D1	2.95	3.05	3.15
D2	2.39	2.49	2.59
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.70	1.80	1.90
e	0.65 BSC		
H	0.30	0.40	0.50
L	0.25	0.40	0.50
a	---	---	15°



DIMENSIONS: MILLIMETERS